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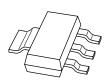
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Kind regards,

Team Nexperia



500 V, 250 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistorRev. 1 — 19 August 2010Product data she

**Product data sheet** 

#### 1. **Product profile**

### 1.1 General description

PNP high-voltage low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

### **1.2 Features and benefits**

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- AEC-Q101 qualified
- Medium power SMD plastic package

### 1.3 Applications

- Electronic ballasts
- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Flyback converters
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	$V_{BE} = 0$	-	-	-500	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-500	V
I <sub>C</sub>	collector current		-	-	-0.25	А
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -50 mA	<u>[1]</u> 80	160	300	

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .



### 500 V, 250 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	collector		2, 4
3	emitter		1
4	collector		3
			sym028

### 3. Ordering information

Table 3.Orde	ring informati	on	
Type number	Package		
	Name	Description	Version
PBHV9050Z	SC-73	plastic surface-mounted package with increased heat sink; 4 leads	SOT223

### 4. Marking

Table 4. Marking codes	
Type number	Marking code
PBHV9050Z	V9050Z

### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		5 - 5 - 7 1	/		
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-500	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-500	V
V <sub>CESM</sub>	collector-emitter peak voltage	$V_{BE} = 0$	-	-500	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-6	V
I <sub>C</sub>	collector current		-	-0.25	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	-0.5	А
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-200	mA

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### 500 V, 250 mA PNP high-voltage low $V_{\mbox{CEsat}}$ (BISS) transistor

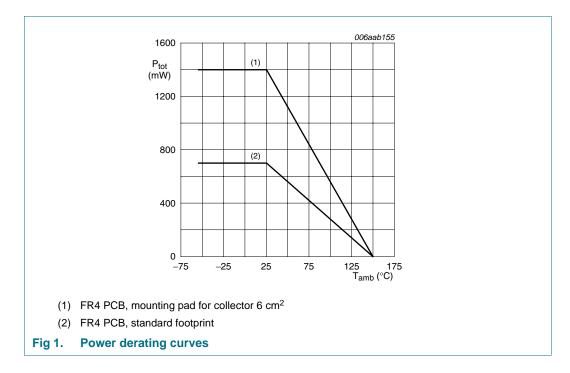
 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub>	total power dissipation	$T_{amb} \leq 25 \ ^{\circ}C$	<u>[1]</u> _	700	mW
			[2] _	1400	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.



### 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	<u>[1]</u> -	-	175	K/W
	junction to ambient		[2] _	-	90	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	20	K/W

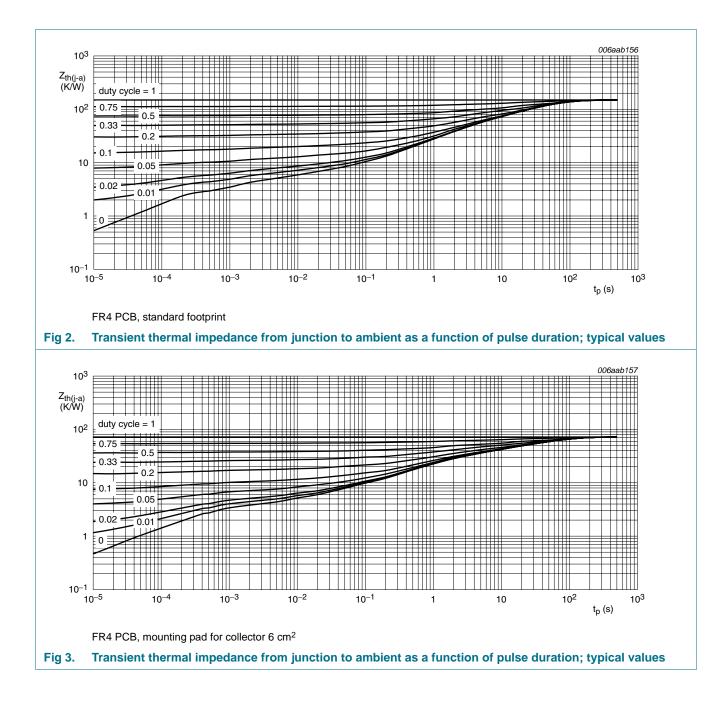
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

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#### 500 V, 250 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor



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### 500 V, 250 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

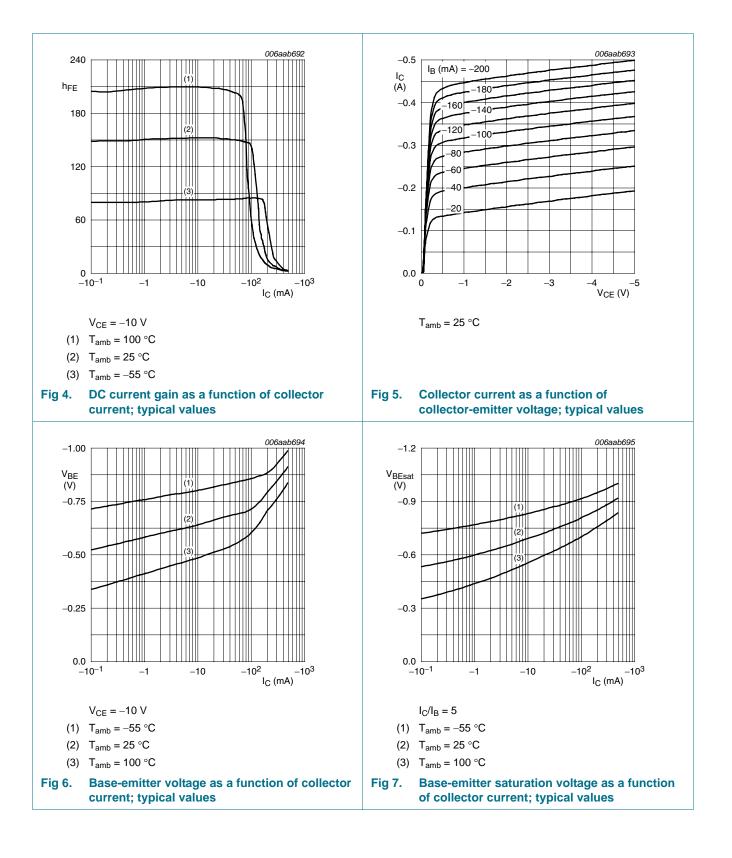
### 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -360 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	-100	nA
	current	$V_{CB} = -360 \text{ V}; I_E = 0 \text{ A};$ T <sub>j</sub> = 150 °C	-	-	-10	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = -360 \text{ V}; \text{ V}_{BE} = 0 \text{ V}$	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -10 \text{ V}$				
		I <sub>C</sub> = -10 mA	[ <u>1]</u> 100	160	300	
		I <sub>C</sub> = -50 mA	<u>[1]</u> 80	160	300	
		I <sub>C</sub> = -100 mA	<u>[1]</u> 70	150	-	
V <sub>CEsat</sub>	collector-emitter	$I_C = -20 \text{ mA}; I_B = -2 \text{ mA}$	<u>[1]</u> -	-115	-200	mV
saturation voltage	saturation voltage	$I_{C} = -50 \text{ mA}; I_{B} = -10 \text{ mA}$	<u>[1]</u> -	-95	-200	mV
	$I_{C} = -100 \text{ mA};$ $I_{B} = -20 \text{ mA}$	<u>[1]</u> _	-140	-350	mV	
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{\rm C} = -50 \text{ mA}; I_{\rm B} = -10 \text{ mA}$	<u>[1]</u> -	-0.75	-0.9	V
t <sub>d</sub>	delay time	$V_{CC} = -20 V;$	-	75	-	ns
t <sub>r</sub>	rise time	I <sub>C</sub> = −0.05 A; - I <sub>Bon</sub> = −5 mA;	-	1600	-	ns
t <sub>on</sub>	turn-on time	$I_{Bon} = -5 \text{ mA},$ $I_{Boff} = 10 \text{ mA}$	-	1675	-	ns
t <sub>s</sub>	storage time		-	1200	-	ns
t <sub>f</sub>	fall time		-	550	-	ns
t <sub>off</sub>	turn-off time		-	1750	-	ns
f <sub>T</sub>	transition frequency	$V_{CE} = -10 \text{ V};$ $I_E = -10 \text{ mA}; \text{ f} = 100 \text{ MHz}$	-	50	-	MHz
C <sub>c</sub>	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = -20 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A}; \\ \text{f} = 1 \text{ MHz} \end{array}$	-	6	-	pF
C <sub>e</sub>	emitter capacitance	V <sub>EB</sub> = -0.5 V; I <sub>C</sub> = i <sub>c</sub> = 0 A; f = 1 MHz	-	170	-	pF

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# **PBHV9050Z**

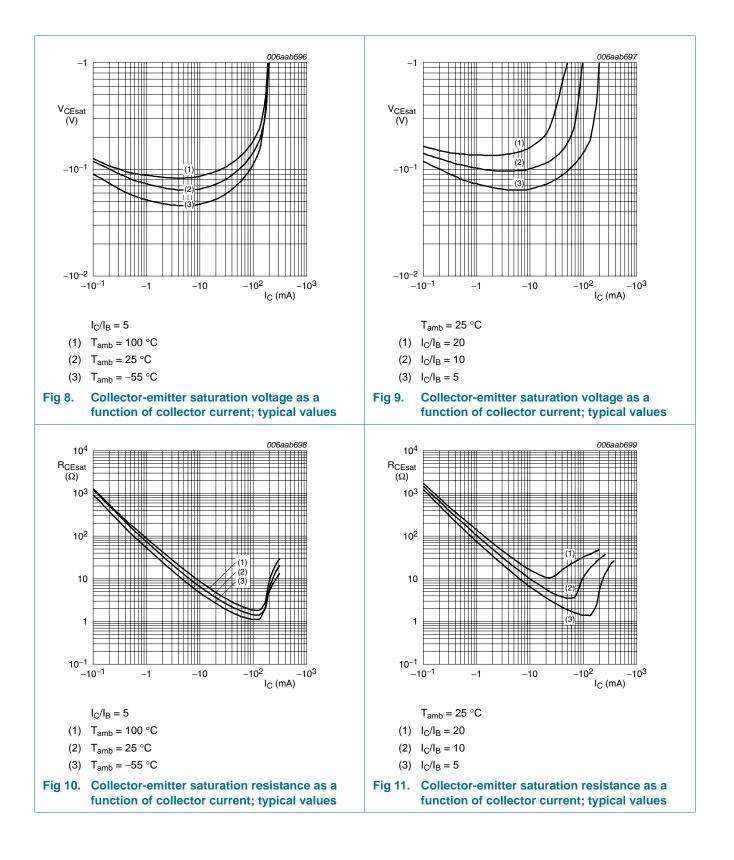
#### 500 V, 250 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor



PBHV9050Z

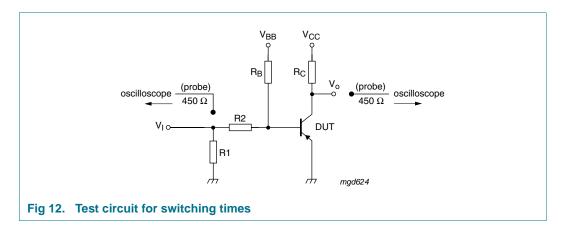
# **PBHV9050Z**

### 500 V, 250 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor



#### 500 V, 250 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

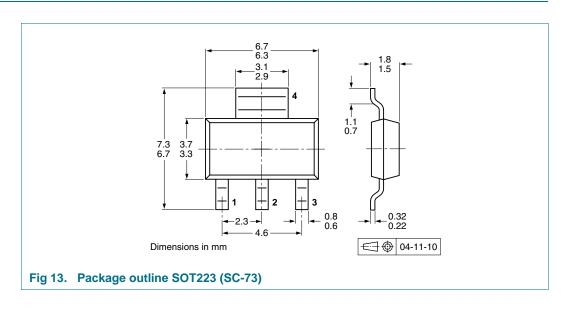
### 8. Test information



### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



### **10. Packing information**

#### Table 8. Packing methods

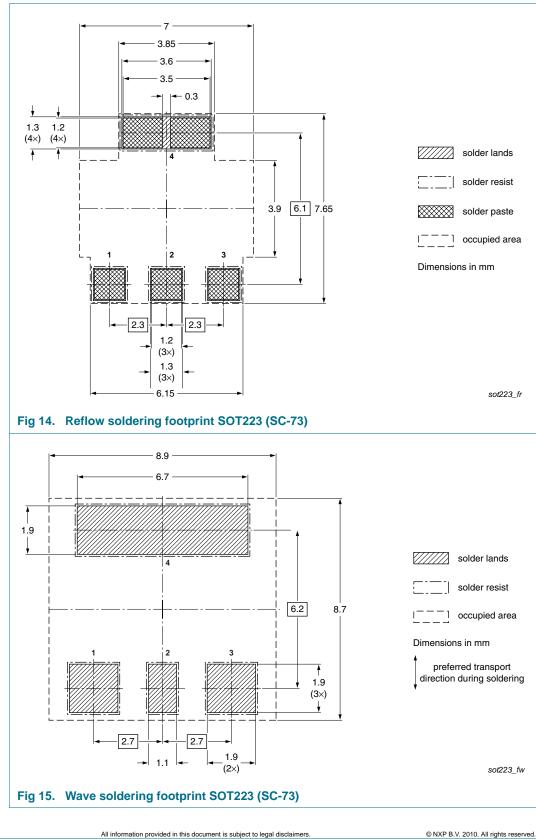
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	ı quantity
			1000	4000
PBHV9050Z	SOT223	8 mm pitch, 12 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

#### 500 V, 250 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

### 11. Soldering



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### 12. Revision history

Table 9. Revision hist	ble 9. Revision history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9050Z v.1	20100819	Product data sheet	-	-

### 13. Legal information

### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Product data sheet

#### 500 V, 250 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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# **PBHV9050Z**

500 V, 250 mA PNP high-voltage low V<sub>CEsat</sub> (BISS) transistor

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